Full Bridge MOSFET Drivers

Mfr.'s Type	Description	Peak Output Current Each Drive	Supply Voltage Bias/Bus (V)	No Load Maint. Supply Current (mA)	Temperature Range (°C)	Package Type
HIP4080AIP	FET Driver with Comparator, Under Voltage, for Class D Amps,Voice Coils, and Motor Control	2.50 A	Bias: 9.5 to 16.0 Bus: 1.0 to 80.0	18.5	–40 to +85	20 Lead PDI
HIP4081AIP	FET Driver with Under Voltage, High Performance for DC-DC Converters, UPS and Motor Control	2.50 A	Bias: 9.5 to 16.0 Bus: 1.0 to 80.0	16.5	–40 to +85	20 Lead PDI
HIP4082IP	FET Driver with Under Voltage Independent FET Control	1.25 A	Bias: 9.5 to 16.0 Bus: 1.0 to 80.0	6.5	–40 to +85	16 Lead PDI

High Performance Buffers

Single

Mfr.'s Type		Description	–3 dB Bandwidth @ Min. Acl (MHz)	Slew Rate (V/µs)	Settling Time (ns to %)	Input Offset Voltage (mV)	Bias Current (µA)	Output Current (mA/Amp)	Supply Range (±V_{DC})	Supply Current (mA/Amp)
PDIP	SOIC									
HFA1112IP	—	850 MHz Programmable Gain (+2, ±1)	850	2050	11-0.10	8	25.0	60	4.5 to 5.5	21.0
HA3-5033-5	—	250 MHz Video Buffer	250	1100	50-0.10	5	20.0	100	5.0 to 16.0	21.0
HA3-5002-5	HA9P5002-5	110 MHz High Output Current	110	1300	50-0.10	5	2.0	220	6.0 to 16.0	8.3

General Purpose Op-Amps

Single

Mfr.'s Type	Description	Minimum Stable Gain	GBWP (MHz)	Slew Rate (V/µs)	Offset Voltage (mV)	Bias Current (µA)	Maximum Supply Voltage (±V)	Supply Current (mA/Amp)	No. of Leads
DIP									
CA3130AE	BiMOS Op-Amp with MOSFET Input/CMOS Output	1	15.0	30.0	2.0	5.000 pA	8.0	2.00	8
CA3130E	BiMOS Op-Amp with MOSFET Input/CMOS Output	1	15.0	30.0	8.0	5.000 pA	8.0	2.00	8
CA3140AE	BiMOS Op-Amp with MOSFET Input/Bipolar Output	1	4.5	9.0	2.0	10.000 pA	18.0	4.00	8
CA3140E	BiMOS Op-Amp with MOSFET Input/Bipolar Output	1	4.5	9.0	5.0	10.000 pA	18.0	4.00	8
HA7-2645-5	High Voltage Op-Amp	1	4.0	5.0	2.0	0.012	50.0	3.20	8
CA3160E	BiMOS Op-Amp with MOSFET Input/CMOS Output	1	4.0	10.0	6.0	5.000 pA	8.0	2.00	8
CA3080E	Operational Transconductance Amplifier (OTA)	1	2.0	75.0	0.4	2.000	18.0	1.00	8
CA741E	High Gain	1	1.0	0.5	1.0	0.080	22.0	1.70	8
HA3-2525-5	Uncompensated High Slew Rate Op-Amp	3	20.0	120.0	5.0	0.125	20.0	4.00	8

Dual

CA3240AE	Dual BiMOS Op-Amp with MOSFET Input/Bipolar Output	1	4.5	9.0	2.0	10.000 pA	18.0	4.00	8
CA3240E	Dual BiMOS Op-Amp with MOSFET Input/Bipolar Output	1	4.5	9.0	5.0	10.000 pA	18.0	4.00	8
CA1458E	High Gain	1	1.0	0.5	1.0	0.080	22.0	1.70	8

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Transistor/Diode Arrays

Transistor Arrays

Mfr.'s Type	Description	$V_{(BR)CEO}$ Min. (V)	$V_{(BR)CBO}$ Min. (V)	h_{FE} Min.	I_C Max. (mA)	Package Type
CA3046	3 Transistors Plus a Differential Pair, fT > 300 MHz, 2 Matched Pairs ±5 mV	15	20	40	50	14 Lead PDIP
CA3081	7 Common Emitter General Purpose NPN High Current Transistors	16	20	40	100	16 Lead PDIP
CA3082	7 Common Collector General Purpose NPN High Current Transistors	16	20	40	100	16 Lead PDIP
CA3083	5 Independent NPN Transistors. Q1 and Q2 Matched; II0 (at 1 mA) 2.5 µA Max.	15	20	40	100	16 Lead PDIP
CA3086	3 Isolated NPN Transistors Plus a Differential Pair. fT>500 MHz Typ. from DC to 120 MHz	15	20	40	50	14 Lead PDIP
CA3146E	3 Transistors Plus a Differential Pair, fT > 500 MHz Typ. Operation from DC to 120 MHz	30	40	40	75	14 Lead PDIP
CA3183AE	5 High Current/High Voltage NPN Transistors. Q1 and Q2 Matched at 1 mA	40	50	40	75	16 Lead PDIP
CA3096E	5 Independent Transistors, 3 NPN and 2 PNP (NPN/PNP)	35/–40	45/–40	150/20	50/–10	16 Lead PDIP
CA3096AE	5 Independent Transistors, 3 NPN and 2 PNP (NPN/PNP)	35/–40	45/–40	150/20	50/–10	16 Lead PDIP
CA3096CE	5 Independent Transistors, 3 NPN and 2 PNP (NPN/PNP)	24/–24	30/–24	100/15	50/–10	16 Lead PDIP
HFA3127B	5 Independent 8 GHz NPN Transistors, NF = 3.5 dB at 1 GHz (NPN/PNP)	8	12	40	40	16 Lead SOIC

Diode Array

Mfr.'s Type	Description	$V_{(BR)R}$ Min. (V)	I_R Max. (µA)	C_D Typ. (pF)	V_{F1}-V_{F2} Max. (mV)	Package Type
CA3039	6 Individual Ultra-Fast Low Capacitance Matched Diodes	5	0.1	0.65	5 (IF=1 mA)	12 Lead TO-5